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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/943,187	08/29/2001	Kristy A. Campbell	MI22-1742	8497
24998 7590 05/28/2004 DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP 2101 L STREET NW			EXAMINER	
			DUONG, KHANH B	
	I, DC 20037-1526		ART UNIT	PAPER NUMBER
		•	2822	
			DATE MAILED: 05/28/2004	1

Please find below and/or attached an Office communication concerning this application or proceeding.

# Supplemental Notic of Allowability

Applicant(s)
CAMPBELL ET AL.
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	Khanh Duong	2822	l pu
The MAILING DATE of this communication appear All claims being allowable, PROSECUTION ON THE MERITS IS (herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIC of the Office or upon petition by the applicant. See 37 CFR 1.313	OR REMAINS) CLOSED or other appropriate comm	vith the correspondence a in this application. If not inc	cluded
1. A This communication is responsive to the communication file			
2.   The allowed claim(s) is/are 1-51.			
3. The drawings filed on 29 August 2001 are accepted by the I	=vaminer		
4. Acknowledgment is made of a claim for foreign priority und			
a) ☐ All b) ☐ Some* c) ☐ None of the:	ier 35 U.S.C. § 119(a)-(d)	or (f).	
	*:		
1. Certified copies of the priority documents have I	been received.		
2. Certified copies of the priority documents have t	peen received in Application	on No	•
3. Copies of the certified copies of the priority docu	uments have been receive	d in this national stage app	lication from the
International Bureau (PCT Rule 17.2(a)).			
* Certified copies not received:		,	•
Applicant has THREE MONTHS FROM THE "MAILING DATE" of noted below. Failure to timely comply will result in ABANDONME THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.	f this communication to file NT of this application.	e a reply complying with the	requirements
<ol> <li>A SUBSTITUTE OATH OR DECLARATION must be submitt INFORMAL PATENT APPLICATION (PTO-152) which gives</li> </ol>	ed. Note the attached EXA reason(s) why the oath or	AMINER'S AMENDMENT or declaration is deficient	r NOTICE OF
6. CORRECTED DRAWINGS ( as "replacement sheets") must i			
(a) ☐ including changes required by the Notice of Draftspersor	o's Patont Drowing Davies	( DTO 040) . (( )	
1) ☐ hereto or 2) ☐ to Paper No./Mail Date	131 atent Diawing Review	v ( P10-946) attached	
(b) including changes required by the office had Francisco de			
<ul><li>(b) ☐ including changes required by the attached Examiner's A</li><li>Paper No./Mail Date</li></ul>	•		
Identifying Indicia such as the application number (see 37 CFR 1.84 each sheet. Replacement sheet(s) should be labeled as such in the	(c)) should be written on the	ne drawings in the front (not	the back) of
DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT FO	OF BIOLOGICAL MATE	EDIAL mount by a rate of the	l. Note the
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Notice of References Cited (PTO-892)	5. Notice of Inf	ormal Patent Application (P	TO-152)
. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)	Dance No. /A	mmary (PTO-413),	
	7. 🛭 Examiner's A	Amendment/Comment	
Examiner's Comment Regarding Requirement for Deposit	8. 🛛 Examiner's S	Statement of Reasons for A	llowance -
of Biological Material	9. 🗌 Other		
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Michael Trinh Primary Examiner

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#### **DETAILED ACTION**

This Office Action is in response to the communication filed February 18, 2004.

#### Information Disclosure Statement

The information disclosure statement (IDS) submitted on April 2, 2004 is considered by the examiner.

#### Examiner's Amendment

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows:

In the Title:

Please amend the title as follows: --METHOD OF FORMING CHALCOGENIDE
COMPRISING DEVICES AND METHOD OF FORMING A PROGRAMMABLE MEMORY
CELL OF MEMORY CIRCUITRY--

### Allowable Subject Matter

Claims 1-51 are allowed.

The following is an examiner's statement of reasons for allowance: none of the prior art of record shows or fairly suggests all the process limitations as claimed. Specifically,

Re claim 1, none of the prior art of record discloses, in addition to other elements or processes as claimed, the steps of: irradiating the silver effective to break a chalcogenide bond of the chalcogenide material at an interface of the silver comprising layer and chalcogenide

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material and diffuse at least some of the silver into the chalcogenide material, and forming an outer surface of the chalcogenide material; after the irradiating, exposing the chalcogenide material outer surface to an iodine comprising fluid effective to reduce roughness of the chalcogenide material outer surface from what it was prior to the exposing; and after exposing, depositing a second electrode material over the chalcogenide material, and forming the second conductive electrode material into an electrode of the device.

Re claim 11, none of the prior art of record discloses, in addition to other elements or processes as claimed, the steps of after forming the chalcogenide comprising material, forming  $Ag_2Se$  over the chalcogenide comprising material; exposing the  $Ag_2Se$  to an iodine comprising fluid effective to etch away at least some of the  $Ag_2Se$ ; and after the exposing, depositing a second conductive electrode material over the chalcogenide material and forming the second conductive electrode material into an electrode of the device.

Re claim 20, none of the prior art of record discloses, in addition to other elements or processes as claimed, the steps of: after forming the chalcogenide comprising material, forming a discontinuous layer of Ag<sub>2</sub>Se over the chalcogenide comprising material; exposing the Ag<sub>2</sub>Se to an iodine comprising fluid effective to etch away at least some of the Ag<sub>2</sub>Se; and after the exposing, depositing a second conductive electrode material over the chalcogenide material, and which is continuous and completely covering at least over the chalcogenide material, and forming the second conductive electrode material into an electrode of the device.

Re claim 26, none of the prior art of record discloses, in addition to other elements or processes as claimed, the steps of irradiating the silver effective to break a chalcogenide bond of the chalcogenide material at an interface of the silver comprising layer and chalcogenide

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material and diffuse at least some of the silver into the chalcogenide material, the irradiating being effective to form a discontinuous layer of  $Ag_2Se$  over the chalcogenide comprising material, the irradiating being effective to maintain the chalcogenide material underlying the  $Ag_2Se$  in a substantially amorphous state; after the irradiating, exposing the  $Ag_2Se$  to an iodine comprising fluid effective to etch away at least a majority of the  $Ag_2Se$ ; and after exposing, depositing a second electrode material over the chalcogenide material, and which is continuous and completely covering at least over the chalcogenide material, and forming the second conductive electrode material into an electrode of the device.

Re claim 34, none of the prior art of record discloses, in addition to other elements or processes as claimed, the steps of: irradiating the metal-containing layer to break a chalcogenide bond of the chalcogenide glass layer at the interface of the metal-containing layer and chalcogenide glass layer, such that at least a portion of the metal-containing layer diffuses into the chalcogenide glass layer; and after the step of irradiating, exposing an outer surface of the chalcogenide glass layer to an iodine comprising fluid, wherein the iodine comprising fluid removes at least a portion of the outer surface that has been irradiated.

Re claim 42, none of the prior art of record discloses, in addition to other elements or processes as claimed, the steps of: irradiating the metal-containing layer to break a chalcogenide bond of the chalcogenide glass layer at the interface of the metal-containing layer and chalcogenide glass layer thereby creating an outside surface; removing at least a portion of the outside surface by etching with an iodine comprising fluid; and, after the step of removing at least a portion of the outside surface, forming a second conductive layer over at least a portion of the outside surface remaining after the act of removing.

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Re claim 51, none of the prior art of record discloses, in addition to other elements or processes as claimed, the steps of: irradiating the metal-containing layer to break a chalcogenide bond of the chalcogenide glass layer at the interface of the metal-containing layer. and chalcogenide glass layer thereby creating an outside surface; the step of irradiating is effective to form Ag<sub>2</sub>Se as at least part of the outside surface; removing at least a portion of the outside surface by etching with an iodine comprising fluid, said etching being effective to etch away at least some of the Ag2Se; and, after the step of removing at least a portion of the outside surface, forming a second conductive layer over at least a portion of the outside surface remaining after the act of removing.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Khanh Duong whose telephone number is (571) 272-1836. The examiner can normally be reached on Monday - Thursday (9:00 AM - 6:00 PM).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian can be reached on (571) 272-1852. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

KBD

Michael Trinh